

Characteristics ($T_j = 25^\circ\text{C}$)
Kennwerte ($T_j = 25^\circ\text{C}$)

		Min.	Typ.	Max.
Drain-Source breakdown voltage – Drain-Source-Durchbruchspannung $I_D = 100 \mu\text{A}$	$V_{(BR)DSS}$	60 V		
Drain-Source leakage current – Drain-Source Leckstrom $V_{DS} = 25 \text{ V}$	G short I_{DSS}			0.5 μA
Gate-Body leakage current – Gate-Substrat Leckstrom $V_{GS} = 15 \text{ V}$	I_{GSS}			10 nA
Gate-Source threshold voltage – Gate-Source Schwellspannung $V_{GS} = V_{DS}, I_D = 1 \text{ mA}$	$V_{GS(th)}$	0.8 V		3 V
Drain-Source on-state resistance – Drain-Source Einschaltwiderstand $V_{GS} = 10 \text{ V}, I_D = 200 \text{ mA}$	$R_{DS(on)}$			5 Ω
Forward Transconductance – Übertragungssteilheit $V_{DS} \geq 2 V_{DS(on)}, I_D = 200 \text{ mA}$	g_{FS}		320 mS	
Input Capacitance – Eingangskapazität $V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{iss}		40 pF	
Output Capacitance – Ausgangskapazität $V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{oss}		30 pF	
Reverse Transfer Capacitance – Rückwirkungskapazität $V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{rss}		10 pF	
Turn-On Time – Einschaltzeit $V_{DD} = 25 \text{ V}, I_D = 500 \text{ mA}, V_{GS} = 10 \text{ V}, R_G = 50 \Omega$	$t_{d(on)}$			10 ns
Turn-Off Delay Time – Ausschaltverzögerung $V_{DD} = 25 \text{ V}, I_D = 500 \text{ mA}, V_{GS} = 10 \text{ V}, R_G = 50 \Omega$	$t_{d(off)}$			10 ns